**Vishay Siliconix** 

## Precision Monolithic Quad SPST Low-Voltage CMOS Analog Switches

#### DESCRIPTION

SHA)

The DG441L, DG442L are low voltage pin-for-pin compatible companion devices to the industry standard DG441L, DG442L with improved performance.

Using BiCMOS wafer fabrication technology allows the DG441L, DG442L to operate on single and dual supplies. Single supply voltage ranges from 3 V to 12 V while dual supply operation is recommended with  $\pm$  3 V to  $\pm$  6 V.

Combining high speed (t<sub>ON</sub>: 20 ns), flat R<sub>DS(on)</sub> over the analog signal range (5  $\Omega$ ), minimal insertion lose (- 3 dB at 280 MHz), and excellent crosstalk and off-isolation performance (- 50 dB at 50 MHz), the DG441L, DG442L are ideally suited for audio and video signal switching.

The DG441L, DG442L responds to opposite control logic as shown in the Truth Table open and two normally closed switches.

### FEATURES

- Halogen-free according to IEC 61249-2-21
  Definition
- 2.7 V thru 12 V single supply or ± 3 V thru ± 6 V dual supply
- On-resistance R<sub>DS(on)</sub>: 17 Ω
- Fast switching t<sub>ON</sub>: 20 ns - t<sub>OFF</sub>: 12 ns
- TTL, CMOS compatible
- Low leakage: 0.25 nA
- 2000 V ESD protection
- Compliant to RoHS Directive 2002/95/EC

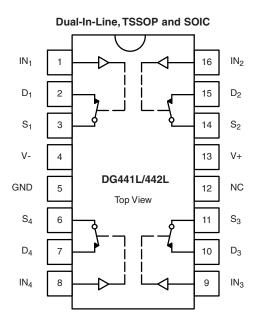
#### BENEFITS

- Widest dynamic range
- Low signal errors and distortion
- Break-before-make switching action
- Simple interfacing

#### **APPLICATIONS**

- Precision automatic test equipment
- Precision data acquisition
- Communication systems
- Battery powered systems
- Computer peripherals
- SDSL, DSLAM
- Audio and video signal routing

### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE								
Logic	DG441L	DG442L						
0	On	Off						
1 Off On								
	•							

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

ORDERING INFORMATION								
Temp. Range	Package	Part Number						
	16-pin TSSOP	DG441LDQ-T1-E3						
- 40 °C to 85 °C	10-pin 1330F	DG442LDQ-T1-E3						
	16-pin narrow	DG441LDY-T1-E3						
	SOIC	DG442LDY-T1-E3						
	16 pip CorDIP	DG441LAK, DG441LAK/883						
- 55 °C to 125 °C	16-pin CerDIP	DG442LAK, DG442LAK/883						
- 55 °C 10 125 °C	LCC-20	DG441LAZ/883						
	LCC-20	DG442LAZ/883						

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HALOGEN

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### **ABSOLUTE MAXIMUM RATINGS** ( $T_A = 25 \,^{\circ}$ C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
V + to V -			- 0.3 to 13	
GND to V - A			7	v
Digital Inputs <sup>a</sup> V <sub>S</sub> , V <sub>D</sub>			GND - 0.3 to (V +) + 0.3 or 30 mA, whichever occurs first	
Continuous Current (any terminal)			30	mA
Current, S or D (pulsed 1 ms, 10 % duty cycle)			100	IIIA
Storage Temperature	(DQ, DY suffix)		- 65 to 125	°C
Storage temperature	(AK suffix)		- 65 to 150	
16-pin TSSOP <sup>c</sup>			450	
Power Dissipation (Packages) <sup>b</sup>	16-pin narrow Body SOIC <sup>d</sup>		650	mW
	16-pin CerDIP <sup>e</sup>		900	

Notes:

a. Signals on  $S_X$ ,  $D_X$ , or  $IN_X$  exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC board.

c. Derate 7 mW/°C above 75 °C d. Derate 7.6 mW/°C above 75 °C

e. Derate 12 mW/°C above 75 °C.

SPECIFICATIONS <sup>a</sup> (Single Supply 12 V)										
		Test Conditions Unless Otherwise Specified			A Suffix Limits - 55 °C to 125 °C		<b>D Suffix</b> - 40 °C	to 85 °C	Unit	
Parameter	Symbol	V + = 12 V, V - = 0 V $V_{IN} = 2.4 V, 0.8 V^{f}$	Temp. <sup>b</sup>	Typ. <sup>c</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	onic	
Analog Switch	1		1		1					
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full		0	12	0	12	V	
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V + = 10.8 V, V - = 0 V $I_S = 10 mA, V_D = 2/9 V$	Room Full	20		30 45		30 40	Ω	
On-Resistance Match Between Channels <sup>e</sup>	$\Delta R_{DS(on)}$	I <sub>S</sub> = 10 mA, V <sub>D</sub> = 9 V	Room	0.1		0.5		0.5	52	
Switch Off Leakage Current	I <sub>S(off)</sub>	V <sub>D</sub> = 1/11 V, V <sub>S</sub> = 11/1 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10		
Switch On Leakage Suitent	I <sub>D(off)</sub>		Room Full		- 1 - 15	1 15	- 1 - 10	1 10	nA	
Channel On Leakage Current	I <sub>D(on)</sub>	$V_{S} = V_{D} = 11/1 V$	Room Full		- 1 - 15	1 15	- 1 - 10	1 10		
Digital Control	•						•			
Input Current, V <sub>IN</sub> Low	I <sub>IL</sub>	V <sub>IN</sub> Under Test = 0.8 V	Full	0.01	- 1.5	1.5	- 1	1		
Input Current, V <sub>IN</sub> High	I <sub>IH</sub>	V <sub>IN</sub> Under Test = 2.4 V	Full		- 1.5	1.5	- 1	1	μA	
Dynamic Characteristics										
Turn-On Time	t <sub>ON</sub>	$R_L = 300 \Omega$ , $C_L = 35 pF$	Room Full	20		60 80		60 70	ns	
Turn-Off Time	t <sub>OFF</sub>	$V_{S} = 5 V$ , see figure 2	Room Full	12		35 50		35 45	ns	
Charge Injection <sup>e</sup>	Q	$V_g$ = 0 V, $R_g$ = 0 $\Omega$ , $C_L$ = 10 nF	Room	5					рС	
Off Isolation <sup>e</sup>	OIRR	$R_1 = 50 \Omega$ , $C_1 = 5 pF$ , f = 1 MHz	Room	71					dB	
Channel-to-Channel Crosstalk <sup>e</sup>	X <sub>TALK</sub>	$n_{\rm L} = 30.32, 0_{\rm L} = 3.01, 1 = 1.0012$	Room	95					uБ	
Source Off Capacitance <sup>e</sup>	C <sub>S(off)</sub>		Room	5						
Drain Off Capacitance <sup>e</sup>	C <sub>D(off)</sub>	f = 1 MHz	Room	6					pF	
Channel On Capacitance <sup>e</sup>	C <sub>D(on)</sub>		Room	15						
Power Supplies	•		•	•		•	•			
Positive Supply Current	l+		Full	0.03		1.5		1		
Negative Supply Current	I-	V <sub>IN</sub> = 0 V or 12 V	Room Full	0.002	- 1 - 7.5		- 1 - 5		μA	
Ground Current	I <sub>GND</sub>		Full	_ 0.002	- 1.5		- 1			

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SPECIFICATIONS <sup>a</sup> (Dual Supply ± 5 V)										
		Test Conditions Unless Otherwise Specified			A Suffix Limits - 55 °C to 125 °C					
Parameter	Symbol	V + = 5 V, V - = -5 V $V_{IN} = 2.4 V, 0.8 V^{f}$	Temp. <sup>b</sup>	Typ. <sup>c</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	onic	
Analog Switch										
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full		- 5	5	- 5	5	V	
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V + = 5 V, V - = - 5 V I <sub>S</sub> = 10 mA, V <sub>D</sub> = $\pm$ 3.5 V	Room Full	20		33 45		33 40	Ω	
On-Resistance Match Between Channels <sup>e</sup>	$\Delta R_{DS(on)}$	$I_{S} = 10 \text{ mA}, V_{D} = \pm 3.5 \text{ V}$	Room	0.1		0.5		0.5	22	
Switch Off	I <sub>S(off)</sub>	V + = 5.5 , V - = - 5.5 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10		
Leakage Current <sup>g</sup>	I <sub>D(off)</sub>	$V_{D} = \pm 4.5 \text{ V}, V_{S} = \pm 4.5 \text{ V}$	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	nA	
Channel On Leakage Current <sup>g</sup>	I <sub>D(on)</sub>	V + = 5.5 V, V - = -5.5 V $V_{S} = V_{D} = \pm 4.5 V$	Room Full		- 1 - 15	1 15	- 1 - 10	1 10		
Digital Control	•	•			•	•				
Input Current, V <sub>IN</sub> Low <sup>e</sup>	I <sub>IL</sub>	V <sub>IN</sub> Under Test = 0.8 V	Full	0.05	- 1.5	1.5	- 1	1	μΑ	
Input Current, V <sub>IN</sub> High <sup>e</sup>	I <sub>IH</sub>	V <sub>IN</sub> Under Test = 2.4 V	Full	0.05	- 1.5	1.5	- 1	1		
Dynamic Characteristics		•			•	•				
Turn-On Time	t <sub>ON</sub>	R <sub>L</sub> = 300 Ω, C <sub>L</sub> = 35 pF	Room Full	21		60 83		60 70	ns	
Turn-Off Time	t <sub>OFF</sub>	$V_S = \pm 3.5$ V, see figure 2	Room Full	16		35 55		35 45	115	
Charge Injection <sup>e</sup>	Q	$V_{g} = 0 V, R_{g} = 0 \Omega, C_{L} = 10 nF$	Room	5					рС	
Off Isolation <sup>e</sup>	OIRR		Room	68						
Channel-to-Channel Crosstalk <sup>e</sup>	X <sub>TALK</sub>	$R_L = 50 \ \Omega$ , $C_L = 5 \ pF$ , f = 1 MHz	Room	85					dB	
Source Off Capacitance <sup>e</sup>	C <sub>S(off)</sub>		Room	9						
Drain Off Capacitance <sup>e</sup>	C <sub>D(off)</sub>	f = 1 MHz	Room	9					pF	
Channel On Capacitance <sup>e</sup>	C <sub>D(on)</sub>		Room	20						
Power Supplies	1		1					1		
Positive Supply Current <sup>e</sup>	l+	4	Full	0.002		1.5		1		
Negative Supply Current <sup>e</sup>	-	V <sub>IN</sub> = 0 V or 5 V	Room Full	- 0.002	- 1 - 7.5		- 1 - 5		μA	
Ground Current <sup>e</sup>	I <sub>GND</sub>		Full	- 0.002	- 1.5		- 1			

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SPECIFICATIONS <sup>a</sup> (Single Supply 5 V)									
		Test Conditions Unless Otherwise Specified				<b>x Limits</b> o 125 °C		<b>to 85 °C</b>	Unit
Parameter	Symbol	V + = 5 V, V - = 0 V V <sub>IN</sub> = 2.4 V, 0.8 V <sup>f</sup>	Temp. <sup>b</sup>	Typ. <sup>c</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	onit
Analog Switch									
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full			5		5	V
Drain-Source On-Resistance <sup>e</sup>	R <sub>DS(on)</sub>	V + = 4.5 V I <sub>S</sub> = 5 mA, V <sub>D</sub> = 1 V, 3.5 V	Room Full	35		50 88		50 75	Ω
On-Resistance Match Between Channels <sup>e</sup>	$\Delta R_{DS(on)}$	I <sub>S</sub> = 10 mA, V <sub>D</sub> = 3.5 V	Room	0.5		1		1	52
Dynamic Characteristics									
Turn-On Time <sup>e</sup>	t <sub>ON</sub>	$R_L = 300 \ Ω$ , $C_L = 35 \ pF$	Room Hot	27		50 90		50 60	ns
Turn-Off Time <sup>e</sup>	t <sub>OFF</sub>	$V_{S}$ = 3.5 V, see figure 2	Room Hot	15		30 55		30 40	115
Charge Injection <sup>e</sup>	Q	$V_{g} = 0 V, R_{g} = 0 \Omega, C_{L} = 10 nF$	Room	0.5					рС
Power Supplies	Power Supplies								
Positive Supply Current <sup>e</sup>	l +		Full	10		200		100	
Negative Supply Current <sup>e</sup>	۱-	V <sub>IN</sub> = 0 V or 5 V	Room Full	- 0.002	- 1 - 7.5		- 1 - 5		μA
Ground Current <sup>e</sup>	I <sub>GND</sub>		Full	- 10	- 200		- 100		



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SPECIFICATIONS <sup>a</sup> (Single Supply 3 V)										
		Test Conditions Unless Otherwise Specified			A Suffix Limits - 55 °C to 125 °C		D Suffix Limits - 40 °C to 85 °C		Unit	
Parameter	Symbol	V + = 3 V, V - = 0 V $V_{IN} = 0.4 V^{f}$	Temp. <sup>b</sup>	Typ. <sup>c</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	onic	
Analog Switch	Analog Switch									
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full		0	3	0	3	V	
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V + = 2.7 V, V - = 0 V I <sub>S</sub> = 5 mA, V <sub>D</sub> = 0.5, 2.2 V	Room Full	65		80 115		80 100	Ω	
On-Resistance Match Between Channels <sup>e</sup>	$\Delta R_{DS(on)}$	I <sub>S</sub> = 5 mA, V <sub>D</sub> = 2.2 V	Room	1		3		3	52	
Switch Off	I <sub>S(off)</sub>	V + = 3.3 , V - = 0 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10		
Leakage Current <sup>g</sup>	I <sub>D(off)</sub>	V <sub>D</sub> = 1, 2 V, V <sub>S</sub> = 2, 1 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	nA	
Channel On Leakage Current <sup>g</sup>	I <sub>D(on)</sub>	V + = 3.3 V, V - = 0 V $V_S = V_D = 1, 2 V$ Fu			- 1 - 15	1 15	- 1 - 10	1 10		
Digital Control										
Input Current, V <sub>IN</sub> Low <sup>e</sup>	Ι <sub>ΙL</sub>	V <sub>IN</sub> under test = 0.4 V	Full	0.005	- 1.5	1.5	- 1	1		
Input Current, V <sub>IN</sub> High <sup>e</sup>	I <sub>IH</sub>	V <sub>IN</sub> under test = 2.4 V	Full	0.005	- 1.5	1.5	- 1	1	μA	
Dynamic Characteristics	1	L	I	<u></u>	1	I	<u> </u>	<u></u>		
Turn-On Time	t <sub>ON</sub>	$R_L = 300 \ Ω, \ C_L = 35 \ pF$	Room Full	50		136 175		136 151	ns	
Turn-Off Time	t <sub>OFF</sub>	$V_{S}$ = 1.5 V, see figure 2	Room Full	30		100 140		100 125	115	
Charge Injection <sup>e</sup>	Q	$V_{g} = 0 V, R_{g} = 0 \Omega, C_{L} = 10 nF$	Room	1					рС	
Off Isolation <sup>e</sup>	OIRR		Room	68						
Channel-to-Channel Crosstalk <sup>e</sup>	X <sub>TALK</sub>	$R_L = 50 $ Ω, $C_L = 5 $ pF , f = 1 MHz	Room	85					dB	
Source Off Capacitance <sup>e</sup>	C <sub>S(off)</sub>		Room	6						
Drain Off Capacitance <sup>e</sup>	C <sub>D(off)</sub>	f = 1 MHz	Room	6					pF	
Channel On Capacitance <sup>e</sup>	C <sub>D(on)</sub>		Room	20						

Notes:

a. Refer to PROCESS OPTION FLOWCHART.

b. Room = 25 °C, Full = as determined by the operating temperature suffix.

c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.

e. Guaranteed by design, not subject to production test.

f.  $V_{IN}$  = input voltage to perform proper function.

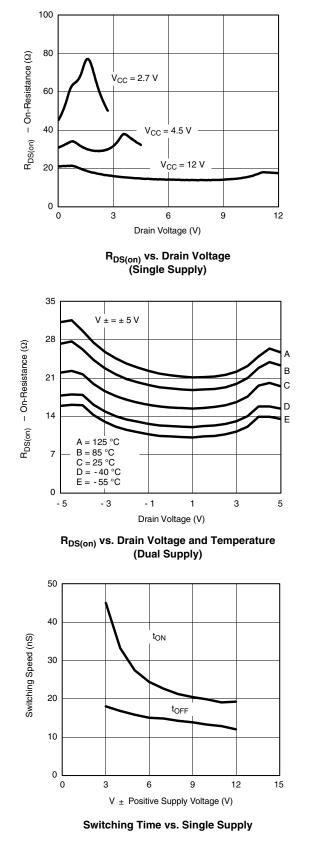
g. Leakage parameters are guaranteed by worst case test conditions and not subject to test.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

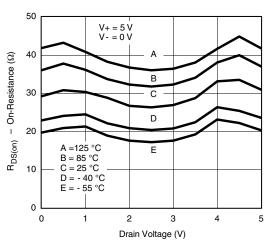
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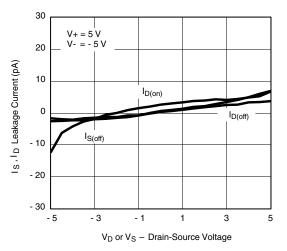
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



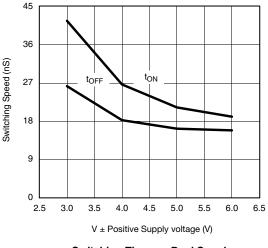
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R<sub>DS(on)</sub> vs. Drain Voltage and Temperature (Single Supply)



Leakage Current vs. Analog Voltage (Dual Supply)



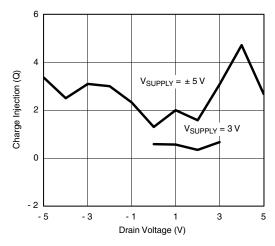
Switching Time vs. Dual Supply

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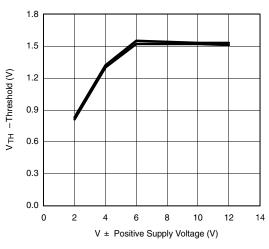


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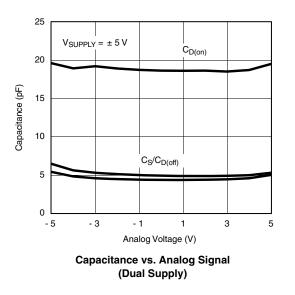
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

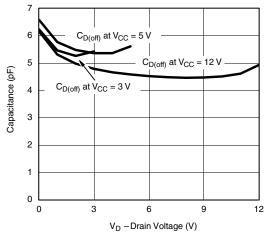


Charge Injection vs. Drain Voltage

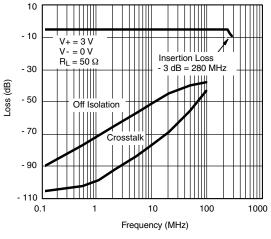


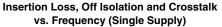
Input Threshold vs. Single Supply Voltage





Drain Capacitance vs. Drain Voltage (Single Supply)





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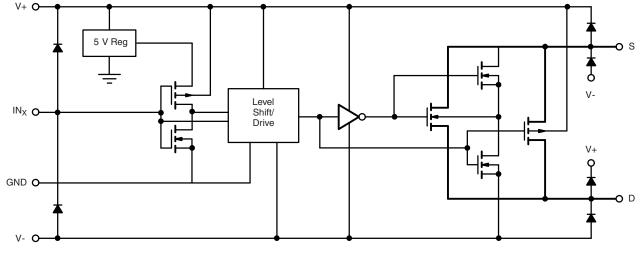
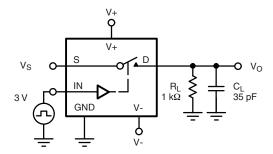
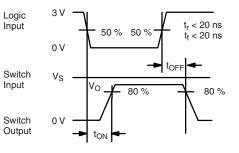


Figure 1.





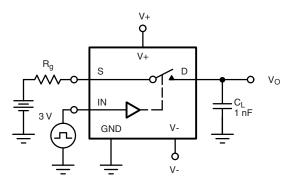
C<sub>L</sub> (includes fixture and stray capacitance)



Logic input waveform is inverted for DG442.

Figure 2. Switching Time

Note:



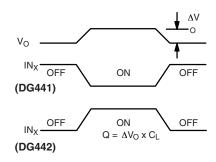


Figure 3. Charge Injection

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### **TEST CIRCUITS**

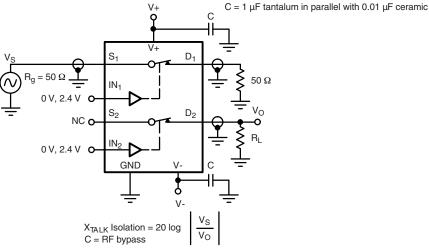
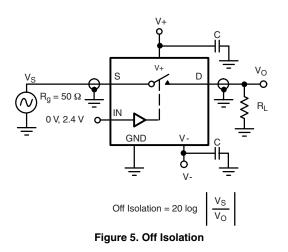


Figure 4. Crosstalk



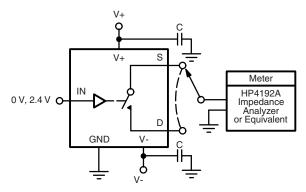


Figure 6. Source/Drain Capacitances

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### **APPLICATIONS**

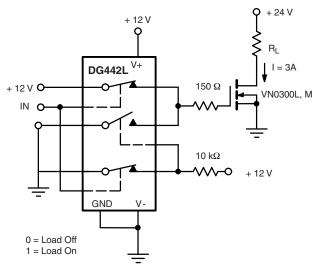
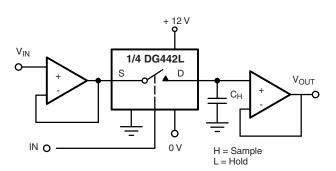
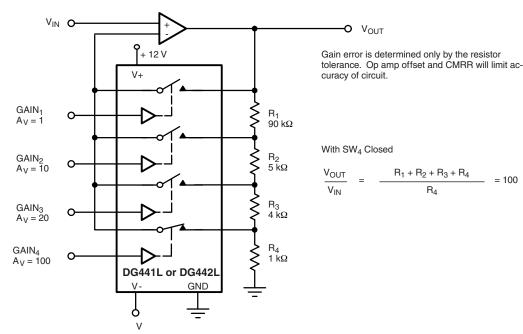


Figure 7. Power MOSFET Driver







• V<sub>OUT</sub>

$$\frac{DUT}{V_{\rm IN}} = \frac{R_1 + R_2 + R_3 + R_4}{R_4} = 100$$

Figure 9. Precision-Weighted Resistor Programmable-Gain Amplifier

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71399.

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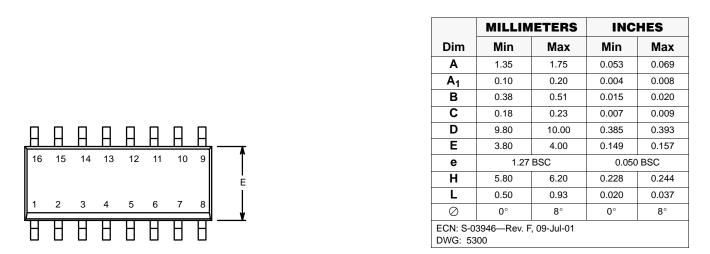
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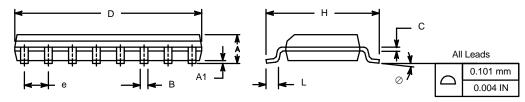


## Package Information Vishay Siliconix

SOIC (NARROW): 16-LEAD

JEDEC Part Number: MS-012



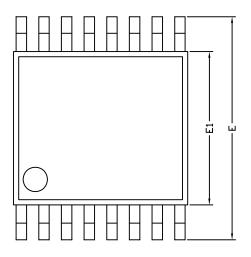


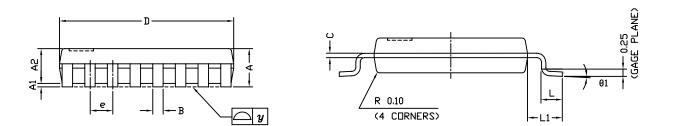


# Package Information

Vishay Siliconix

## TSSOP: 16-LEAD





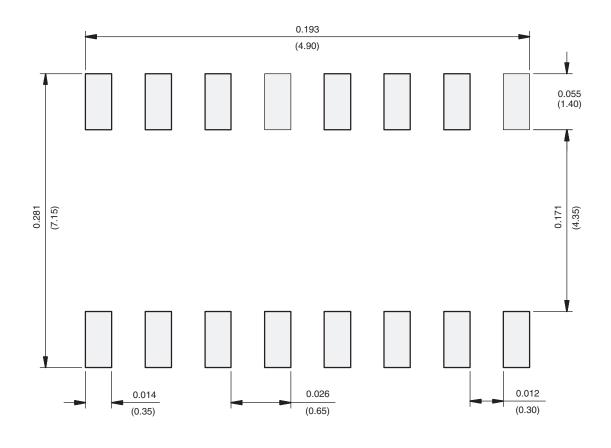
	DIMENSIONS IN MILLIMETERS							
Symbols	Min	Nom	Max					
A	-	1.10	1.20					
A1	0.05	0.10	0.15					
A2	-	1.00	1.05					
В	0.22	0.28	0.38					
С	-	0.127	-					
D	4.90	5.00	5.10					
E	6.10	6.40	6.70					
E1	4.30	4.40	4.50					
е	-	0.65	-					
L	0.50	0.60	0.70					
L1	0.90	1.00	1.10					
у	-	-	0.10					
θ1	0°	3°	6°					
ECN: S-61920-Rev. D, 23 DWG: 5624	-Oct-06							



**PAD** Pattern

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#### **RECOMMENDED MINIMUM PAD FOR TSSOP-16**



Recommended Minimum Pads Dimensions in inches (mm)

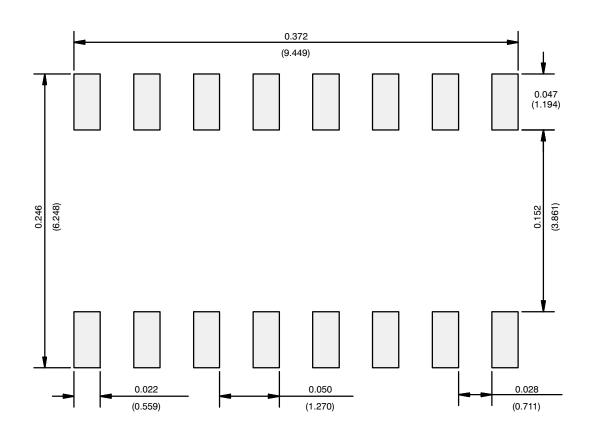
Revision: 02-Sep-11

# **Application Note 826**

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### **RECOMMENDED MINIMUM PADS FOR SO-16**



Recommended Minimum Pads Dimensions in Inches/(mm)

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